DATAFILE FOLDER DF4109



# MASTR<sup>®</sup> Personal Series

PE MODELS
SYSTEMS BOARD AND CASE ASSEMBLY 19D417103G4
(5 - FREQUENCY WITH TYPE 99 DECODER)



# **SPECIFICATIONS** \*

MODEL NUMBERS

19D417103G4

CONTROLS

30-50 MHz

Volume ON-OFF Switch
Squelch Control
Five-Frequency Selector Switch
PTT Switch
Tone Option Switch
Collapsible Antenna
Accessory Jack

\*These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

# LBI4700

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500 m

--- WARNING ---

No one should be permitted to handle any portion of the equipment that is supplied with high voltage; or to connect any external apparatus to the units while the units are supplied with power. KEEP AWAY FROM LIVE CIRCUITS.

# DESCRIPTION

System Board A704 provides system interconnections between the transmitter, receiver tone options and operating controls in the 30 to 50 MHz, Five-Frequency with Type 99 Decoder PE Models. The System Board contains transmitter oscillator modules A4 through A8 and receiver oscillator modules A9 through A11. In addition to the oscillator modules, the system board contains Audio Module A1, 5.4 Volt Regulator Module A2, Filter Module A3, optional Compressor Module A50, system relay K1 and audio and DC switching circuitry.

Jacks J702 and J703 are connected to the system board and provide contacts for an external antenna, speaker, and microphone. J702 provides contacts for the external antenna and speaker, and J703 provides contacts for an external microphone. Placing the radio into the vehicular charger automatically connects the jack contacts to the external circuitry. The radio is also connected to the external antenna when placed in the desk charger.

# CIRCUIT ANALYSIS

# AUDIO SWITCHING

Audio switching for the Speaker/Microphone LS1 is controlled by diode CR5 as shown in Figure 1.

Pressing PTT switch S701 forward biases diode CR5, permitting audio from LS1 to be applied to transmitter audio module A1.

Keying the external microphone permits audio to be applied directly to the transmitter audio module.

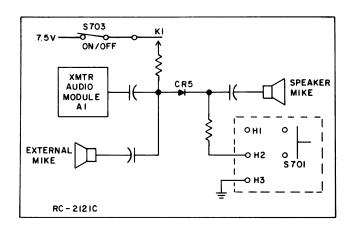


Figure 1 - Audio Switching Circuit

## DC SWITCHING

Operation of system relay K1 is controlled by diode CR2 (see Figure 2).

Pressing S701 forward biases CR2, completing the relay path to ground. This energizes relay K1, and switches the battery voltage to the transmitter audio and regulator modules. Energizing K1 also connects the transmitter output to the antenna.

# PTT SWITCH (A705)

Solid State PTT switch S701 forward biases diode CR2 to energize relay K1 and key the radio. When S701 is pressed PNP, transistor Q1 conducts. Transistor Q1

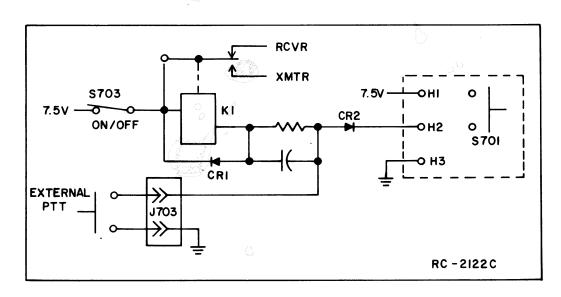


Figure 2 - DC Switching Circuit



conducting applies a positive voltage to the base of NPN transistor Q2, causing Q2 to also conduct. Transistor Q2 conducting, provides a conduction path to ground for diode CR2. Relay K1 is energized and the radio is keyed.

# REPEATING OSCILLATOR MODULES

Both the transmitter and receiver can be adapted to repeat the use of the same frequency without the use of additional Oscillator Modules. The Oscillator Module is replaced by a diode, allowing the frequency selector switch to have the same frequency on one or more switch positions even though only one Oscillator Module is used for each of the repeated channels. A typical diagram with repeated Oscillator Modules is shown in Figure 3.

Complete instructions for multifrequency modifications are contained in the Multi-Frequency Modification Diagram (see Table of Contents).

For radios equipped with Channel Cuard, Type 90 Encoders/Decoders or Type 99 Decoders, repeating Oscillator Modules also permits switching or disabling tones on the same RF frequency with the multi-frequency switch. Also, the tone and RF frequency can be changed at the same time.

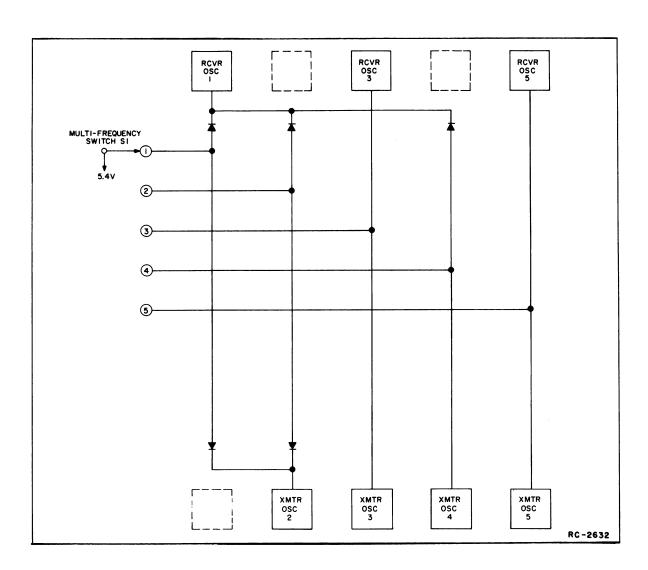
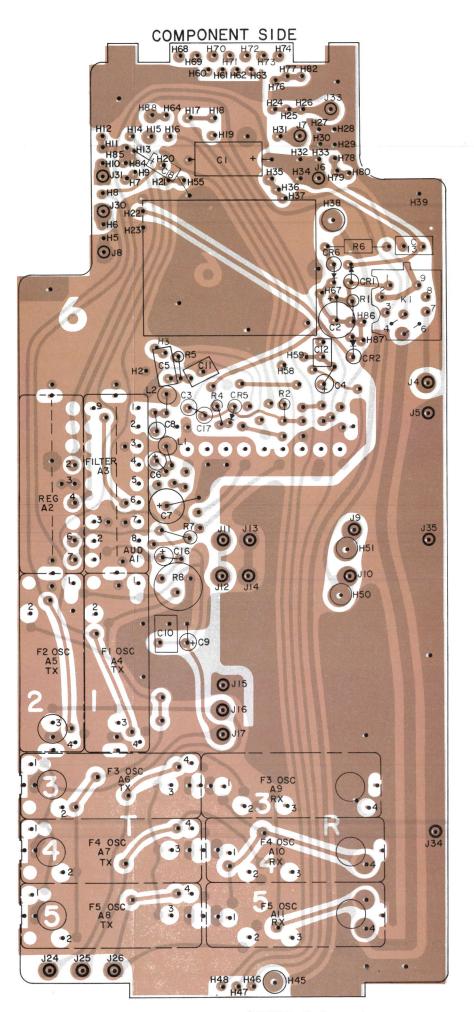
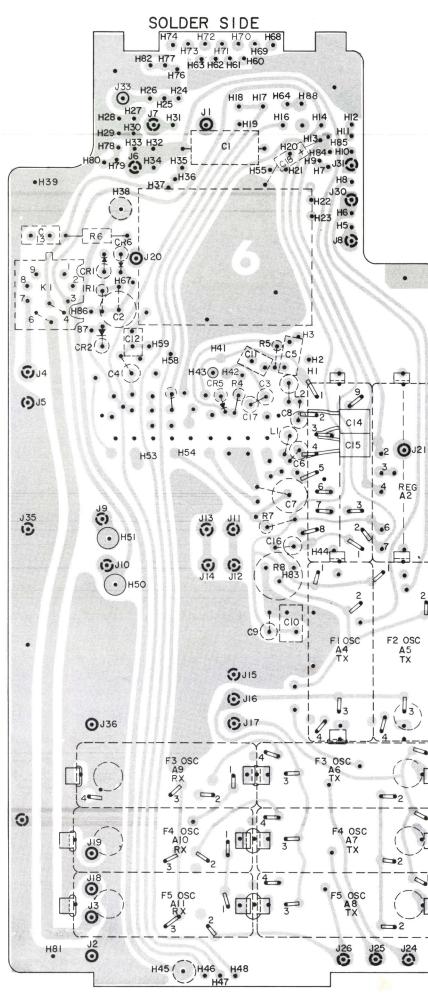
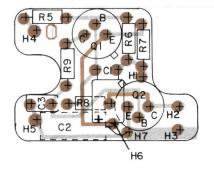


Figure 3 - Repeating Oscillator Modules





A 705

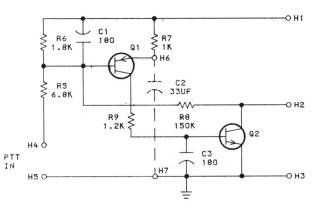


LEAD IDENTIFICATION FOR QI AND Q2



OR
IN-LINE TRIANGULAR
TOP VIEW
NOTE, LEAD ARRANGEMENT, AND NOT
CASE SHAPE, IS DETERMINING
FACTOR FOR LEAD IDENTIFICATION

(19B233296, Rev. 0) (19B232970, Sh. 1, Rev. 0) (19B232970, Sh. 2, Rev. 1)



NOTE: C2 IS PART OF KIT 19A136579

ALL RESISTORS ARE 1/8 WATT UNLESS
OTHERWISE SPECIFIED AND RESISTOR
VALUES IN OHMS UNLESS FOLLOWED BY
K-1000 OHMS OR MEG-1,000,000 OHMS.
CAPACITOR VALUES IN PICOFARADS (EQUAL
TO MICROMICROFARADS) UNLESS FOLLOWED
BY UF-MICROFARADS. INDUCTANCE VALUES
IN MICROHENRYS UNLESS FOLLOWED BY
MH-MILLIHENRYS OR H-HENRYS.

(19B232959, Rev. 1)

# **OUTLINE DIAGRAM**

RUNS ON BOTH SIDES

30-50 MHz SYSTEM BOARD

- RUNS ON SOLDER SIDE

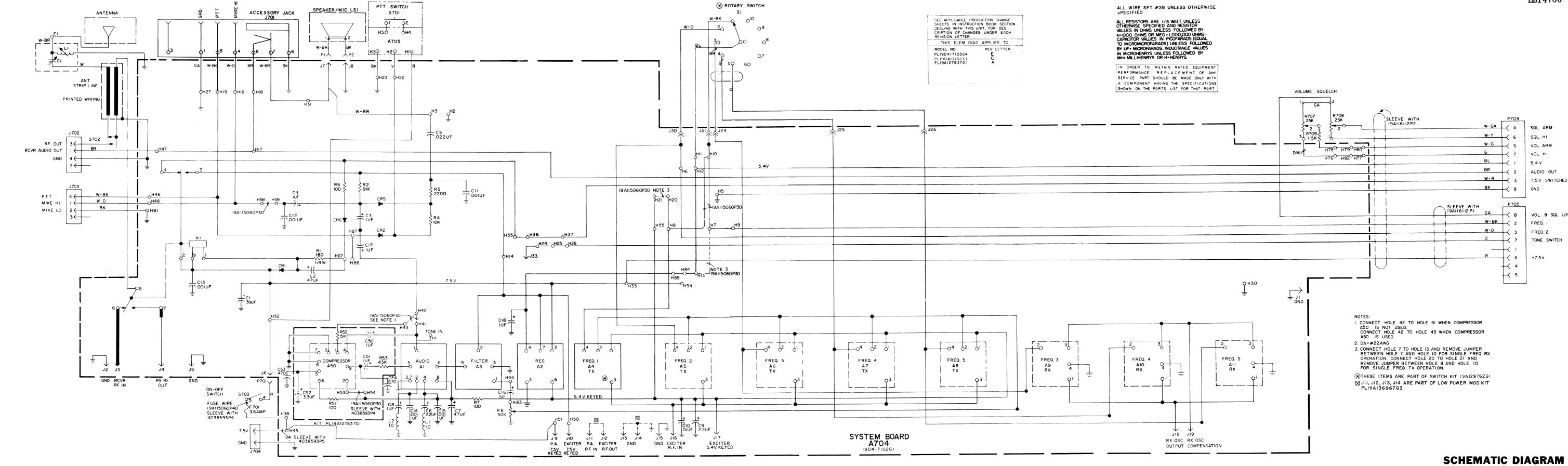
- RUNS ON COMPONENT SIDE

Issue 4

(19D416986, Sh. 2, Rev. 6)

(19D417964, Rev. 5)

(19D416986, Sh. 2, Rev. 6)



30—50 MHz SYSTEM BOARD

LBI 4700

PARTS LIST

### A	SYMBOL	GE PART NO.	DESCRIPTION		
19C328070G1   S.4 Volt Regulator Module.	A704				
In REV B & earlier:  5.4 Volt Regulator Module.  Post Limiter Filter.  NOTE: When reordering A4-A8, give GE Part Number and exact crystal frequency. Crystal Freq = Operating Freq  A4  4EG31A10  Transmitter Oscillator.  NOTE: When reordering A9-A11, give GE Part Number exact crystal frequency.  Crystal Freq. (30-36 MHz) = F0 +20  3  Crystal Freq. (30-36 MHz) = F0 +20  3  Crystal Freq. (36-42 MHz) = F0 +20  3  Crystal Freq. (42-50 MHz) = F0 +20  3  Crystal Freq. (42-50 MHz) = F0 +20  4EG28A18  Receiver Oscillator. (36-42 MHz)	Al	19C32O354G1	Transmitter Audio Module.		
19C31190562   5.4 Volt Regulator Module.	A2*	19C328070G1			
NOTE: When reordering A4-A8, give GE Part Numand exact crystal frequency. Crystal Freq = Operating Freq		19C311905G2			
### A	A3	19C320345G1	Post Limiter Filter.		
NOTE: When reordering A9-All, give GE Part Number exact crystal frequency.			Operating Freq		
Number exact crystal frequency.   Crystal Freq. (30-36 MHz) = Fo +20 / 3	thru	4EG31A10	Transmitter Oscillator.		
Crystal Freq. (36-42 MHz) = \( \frac{fo \text{ + 23}}{3} \)  Crystal Freq. (42-50 MHz) = \( \frac{fo \text{ + 20}}{3} \)  Crystal Freq. (42-50 MHz) = \( \frac{fo \text{ + 20}}{3} \)  Receiver Oscillator. (30-36 MHz, 42-50 MHz)  Receiver Oscillator. (36-42 MHz)			NOTE: When reordering A9-All, give GE Part Number exact crystal frequency.		
Crystal Freq. (42-50 MHz) = \( \frac{\chi_2}{3} \)  A9 thru A11  4EG28A17  Receiver Oscillator. (30-36 MHz, 42-50 MHz)  Receiver Oscillator. (36-42 MHz)			Crystal Freq. $(30-36 \text{ MHz}) = \frac{\text{Fo} + 20}{3}$		
A9 thru A11 4EG28A18 Receiver Oscillator. (30-36 MHz, 42-50 MHz) Receiver Oscillator. (36-42 MHz)			Crystal Freq. $(36-42 \text{ MHz}) = \frac{\text{Fo} + 23}{3}$		
### Thru All ### 4EG28A18  Receiver Oscillator. (36-42 MHz)			Crystal Freq. (42-50 MHz) = $\frac{\text{Fo} + 20}{3}$		
A11		4EG28A17	Receiver Oscillator. (30-36 MHz, 42-50 MHz)		
C1 5491674P30 Tantalum: 39 µf ±20%, 10 VDCW; sim to Sprague Type 162D.  C2 5491674P42 Tantalum: 47 µf ±20%, 6 VDCW; sim to Sprague Type 162D.  C3 5491674P1 Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C5 19A116244P2 Ceramic: 0.022 µf ±20%, 50 VDCW.  C6 5491674P8 Tantalum: 2.2 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C7 5491674P42 Tantalum: 47 µf ±20%, 6 VDCW; sim to Sprague Type 162D.  C8 5491674P1 Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C9 5491674P8 Tantalum: 2.2 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C10 19A116192P1 Ceramic: 0101 µf ±20%, 50 VDCW; sim to Erie 8121 SPECIAL.  C11 5495323P12 Ceramic: .001 µf +100% -20%, 75 VDCW.  C15 5491674P28 Tantalum: 1.0 µf +20%, 25 VDCW; sim to Sprague Type 162D.  C16 5491674P1 Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C17 5491674P1 Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C18* 5491674P1 Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C18* 5491674P1 Silicon, fast recovery, 225 mA, 50 PIV.  CR1 19A115250P1 Silicon; sim to Type 1N1200A.		4EG28A18	Receiver Oscillator. (36-42 MHz)		
Type 162D.  Tantalum: 47 µf ±20%, 6 VDCW; sim to Sprague Type 162D.  Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C5 19A116244P2 Ceramic: 0.022 µf ±20%, 50 VDCW.  C6 5491674P8 Tantalum: 2.2 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C7 5491674P42 Tantalum: 47 µf ±20%, 6 VDCW; sim to Sprague Type 162D.  C8 5491674P1 Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C9 5491674P8 Tantalum: 2.2 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C10 19A116192P1 Ceramic: 0101 µf ±20%, 50 VDCW; sim to Erie 8121 SPECIAL.  C11 5495323P12 Ceramic: .001 µf ±20%, 50 VDCW; sim to Erie 8121 SPECIAL.  C16 5491674P28 Tantalum: 1.0 µf ±20%, 25 VDCW; sim to Sprague Type 162D.  C17 5491674P1 Tantalum: 1.0 µf ±20%, 25 VDCW; sim to Sprague Type 162D.  C18* 5491674P1 Tantalum: 1.0 µf ±40-20%, 10 VDCW; sim to Sprague Type 162D.  C18* 5491674P1 Tantalum: 1.0 µf ±40-20%, 10 VDCW; sim to Sprague Type 162D.  C18* 5491674P1 Silicon; sim to Type 1812OOA.					
Type 162D.  C3 and C4  C5 19A116244P2	Cl	5491674P30			
Sprague Type 162D.  C5 19Al16244P2 Ceramic: 0.022 \( \text{\psi} \) \( \text{t} \) 20%, 50 VDCW.  C6 5491674P8 Tantalum: 2.2 \( \text{\psi} \) \( \text{t} \) 40-20%, 10 VDCW; sim to Sprague Type 162D.  C7 5491674P42 Tantalum: 47 \( \text{\psi} \) \( \text{t} \) 20%, 6 VDCW; sim to Sprague Type 162D.  C8 5491674P1 Tantalum: 1.0 \( \text{\psi} \) \( \text{t} \) 40-20%, 10 VDCW; sim to Sprague Type 162D.  C9 5491674P8 Tantalum: 2.2 \( \text{\psi} \) \( \text{t} \) 40-20%, 10 VDCW; sim to Sprague Type 162D.  C10 19Al16192P1 Ceramic: 0101 \( \text{\psi} \) \( \text{t} \) 220%, 50 VDCW; sim to Erie 8121 SPECIAL.  C11 5495323P12 Ceramic: 001 \( \text{\psi} \) \( \text{t} \) 100% -20%, 75 VDCW.  C16 5491674P28 Tantalum: 1.0 \( \text{\psi} \) \( \text{t} \) +20%, 25 VDCW; sim to Sprague Type 162D.  C17 5491674P1 Tantalum: 1.0 \( \text{\psi} \) \( \text{t} \) +40-20%, 10 VDCW; sim to Sprague Type 162D.  C18* 5491674P1 Tantalum: 1.0 \( \text{\psi} \) \( \text{t} \) 40-20%, 10 VDCW; sim to Sprague Type 162D. Added by REV C.  DIODES AND RECTIFIERS  CR1 19Al15250P1 Silicon; sim to Type 1N1200A.	C2	5491674P42	Tantalum: 47 $\mu$ f $\pm 20\%$ , 6 VDCW; sim to Sprague Type 162D.		
Tantalum: 2.2 μf +40-20%, 10 VDCW; sim to Sprague Type 162D.  Tantalum: 47 μf ±20%, 6 VDCW; sim to Sprague Type 162D.  Tantalum: 1.0 μf +40-20%, 10 VDCW; sim to Sprague Type 162D.  Tantalum: 1.0 μf +40-20%, 10 VDCW; sim to Sprague Type 162D.  Tantalum: 2.2 μf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C10 19A116192P1 Ceramic: 0101 μf ±20%, 50 VDCW; sim to Erie 8121 SPECIAL.  C11 5495323P12 Ceramic: .001 μf +100% -20%, 75 VDCW.  C16 5491674P28 Tantalum: 1.0 μf +20%, 25 VDCW; sim to Sprague Type 162D.  C17 5491674P1 Tantalum: 1.0 μf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C18* 5491674P1 Tantalum: 1.0 μf +40-20%, 10 VDCW; sim to Sprague Type 162D. Added by REV C.  DIODES AND RECTIFIERS  CR1 19A115250P1 Silicon, fast recovery, 225 mA, 50 PIV.	and	5491674P1	Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.		
Sprague Type 162D.  C7 5491674P42 Tantalum: 47 µf ±20%, 6 VDCW; sim to Sprague Type 162D.  C8 5491674P1 Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C9 5491674P8 Tantalum: 2.2 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C10 19A116192P1 Ceramic: 0101 µf ±20%, 50 VDCW; sim to Erie 8121 SPECIAL.  C11 5495323P12 Ceramic: .001 µf +100% -20%, 75 VDCW.  C15 5491674P28 Tantalum: 1.0 µf +20%, 25 VDCW; sim to Sprague Type 162D.  C17 5491674P1 Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C18* 5491674P1 Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D. Added by REV C.  DIODES AND RECTIFIERS  CR1 19A115250P1 Silicon, fast recovery, 225 mA, 50 PIV.	C5	19A116244P2			
Sprague Type 162D.  C8 5491674P1 Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C9 5491674P8 Tantalum: 2.2 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C10 19A116192P1 Ceramic: 0101 µf ±20%, 50 VDCW; sim to Erie 8121 SPECIAL.  C11 5495323P12 Ceramic: .001 µf +100% -20%, 75 VDCW.  C15 5491674P28 Tantalum: 1.0 µf +20%, 25 VDCW; sim to Sprague Type 162D.  C17 5491674P1 Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C18* 5491674P1 Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D. Added by REV C.  DIODES AND RECTIFIERS  CR1 19A115250P1 Silicon, fast recovery, 225 mA, 50 PIV.  CR2 5495922P1 Silicon; sim to Type 1N1200A.	C6	5491674P8			
Sprague Type 162D.  C9 5491674P8 Tantalum: 2.2 \( \pm f \) +40-20\( \pm h \) 10 VDCW; sim to Sprague Type 162D.  C10 19A116192P1 Ceramic: 0101 \( \pm f \) ±20\( \pm h \), 50 VDCW; sim to Erie 8121 SPECIAL.  C11 thru C15  C16 5491674P28 Tantalum: 1.0 \( \pm f \) +20\( \pm h \), 75 VDCW.  C17 5491674P1 Tantalum: 1.0 \( \pm f \) +40-20\( \pm h \), 10 VDCW; sim to Sprague Type 162D.  C18* 5491674P1 Tantalum: 1.0 \( \pm f \) +40-20\( \pm h \), 10 VDCW; sim to Sprague Type 162D.  C18* 5491674P1 Tantalum: 1.0 \( \pm f \) +40-20\( \pm h \), 10 VDCW; sim to Sprague Type 162D. Added by REV C.  DIODES AND RECTIFIERS  CR1 19A115250P1 Silicon, fast recovery, 225 mA, 50 PIV.  CR2 5495922P1 Silicon; sim to Type 1N1200A.	C7	5491674P42	Tantalum: 47 $\mu$ f $\pm 20\%$ , 6 VDCW; sim to Sprague Type 162D.		
Sprague Type 162D.  C10 19Al16192P1 Ceramic: 0101 µf ±20%, 50 VDCW; sim to Erie 8121 SPECIAL.  C11 thru C15  C16 5491674P28 Tantalum: 1.0 µf +20%, 25 VDCW; sim to Sprague Type 162D.  C17 5491674P1 Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C18* 5491674P1 Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C18* 5491674P1 Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D. Added by REV C.  DIODES AND RECTIFIERS  CR1 19Al15250P1 Silicon, fast recovery, 225 mA, 50 PIV.  CR2 5495922P1 Silicon; sim to Type 1N1200A.	C8	5491674Pl	Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.		
8121 SPECIAL.  C11 thru C15  C16  5491674P28  Tantalum: 1.0 \( \text{pf} \) +20\( \text{m} \), 25 VDCW; sim to Sprague Type 162D.  C17  5491674P1  Tantalum: 1.0 \( \text{pf} \) +40-20\( \text{m} \), 10 VDCW; sim to Sprague Type 162D.  C18*  5491674P1  Tantalum: 1.0 \( \text{pf} \) +40-20\( \text{m} \), 10 VDCW; sim to Sprague Type 162D.  C18*  5491674P1  Tantalum: 1.0 \( \text{pf} \) +40-20\( \text{m} \), 10 VDCW; sim to Sprague Type 162D. Added by REV C.  DIODES AND RECTIFIERS  CR1  19A115250P1  Silicon, fast recovery, 225 mA, 50 PIV.  CR2  5495922P1  Silicon; sim to Type 1N1200A.	С9	5491674P8	Tantalum: 2.2 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.		
thru C15  C16	C10	19A116192P1	Ceramic: 0101 $\mu$ f $\pm$ 20%, 50 VDCW; sim to Erie 8121 SPECIAL.		
Sprague Type 162D.  C17 5491674P1 Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D.  C18* 5491674P1 Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D. Added by REV C.  DIODES AND RECTIFIERS  CR1 19A115250P1 Silicon, fast recovery, 225 mA, 50 PIV.  CR2 5495922P1 Silicon; sim to Type 1N1200A.	thru	5495323P12	Ceramic: .001 µf +100% -20%, 75 YDCW.		
Sprague Type 162D.  C18* 5491674P1 Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D. Added by REV C.  DIODES AND RECTIFIERS  CR1 19A115250P1 Silicon, fast recovery, 225 mA, 50 PIV.  CR2 5495922P1 Silicon; sim to Type 1N1200A.	C16	5491674P28	Tantalum: 1.0 µf +20%, 25 VDCW; sim to Sprague Type 162D.		
Sprague Type 162D. Added by REV C.  DIODES AND RECTIFIERS  CRI 19All5250Pl Silicon, fast recovery, 225 mA, 50 PIV.  CR2 5495922Pl Silicon; sim to Type 1N1200A.	C17	5491674P1	Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to		
CRl 19Al15250Pl Silicon, fast recovery, 225 mA, 50 PIV. CR2 5495922Pl Silicon; sim to Type lNl200A.	C18*	5491674P1	Tantalum: 1.0 µf +40-20%, 10 VDCW; sim to Sprague Type 162D. Added by REV C.		
CR2 5495922P1 Silicon; sim to Type lN1200A.					
	CRl	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.		
1 1	CR2	5495922P1	Silicon; sim to Type lN1200A.		
CR5 5495922Pl Silicon; sim to Type 1N1200A.	CR5	5495922P1	Silicon; sim to Type lN1200A.		
	CR6				

\*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
		JACKS AND RECEPTACLES			TRANSISTORS			
Jl* thru	19A116366P4	Contact, electrical: sim to Concord 10-891-1.	Q1	19A129187P1	Silicon, PNP.	S701		See Mechanical Parts RC2623, items 36-42.
J5*			Q2	19A116201P3	Silicon, NPN.	S702	1	See Mechanical Parts RC2623, items 43-50.
		Earlier than REV A:	İ		RESISTORS	S703		(Part of R707).
	19A116366P1	Contact, electrical: sim to Cambion 460-3232-01-03.	R5	3R151P682J	Composition: 6.8K ohms ±5%, 1/8 w.	S704*	19A116648P5	Toggle: SPDT, sim to C and K Components 7107SDG. Deleted by REV B.
J6	19A116366P2	Contact, electrical: sim to Cambion 460-3233-01-	R6	3R151P182J	Composition: 1.8K ohms ±5%, 1/8 w.			
thru J8		03.	R7	3R151P102J	Composition: 1K ohms ±5%, 1/8 w.			
J9*	19A116366P4	Contact, electrical: sim to Concord 10-891-1.	R8	3R151P154J	Composition: 150K ohms ±5%, 1/8 w.			ASSOCIATED ASSEMBLIES
thru J21*			R9	3R151P122J	Composition: 1.2K ohms ±5%, 1/8 w.			FRONT COVER ASSEMBLY 19C317416G2 STANDARD
		Earlier than REV A:			DUGU TO THE WATER DOLD			19C317416G2 STANDARD 19C317416G6 HI POWER
	19A116366P1	Contact, electrical: sim to Cambion 460-3232-01-03.	A705*		PUSH TO TALK SWITCH BOARD 19B232586G1			LOUDSPEAKERS
J24*	19A116366P4	Contact, electrical: sim to Concord 10-891-1.			(Added by REV E) (Deleted by REV F)	LS1	19A116090P1	Permanent magnet: 2.00 inch, 8 ohms ±10% voice
thru J26*						1201	19411609091	coil imp, 450 Hz ±112 Hz resonant; freq range 400 to 3000 Hz.
	19A116366P1	Earlier than REV A:	Cl	19A116114P10073	Ceramic: 180 pf ±10%, 100 VDCw; temp coef			400 to 3000 nz.
	19411036661	Contact, electrical: sim to Cambion 460-3232-01-03.	"	194116114910073	-3300 PPM.			
J30*	19A116366P4	Contact, electrical: sim to Concord 10-891-1.	сз	19A116114P10073	Ceramic: 180 pf ±10%, 100 VDCW; temp coef -3300 PPM.	Pl and	19A115834P4	Contact, electrical: sim to AMP 2-332070-9.
and J31*		Doubles the DDV A.	C4*	19A116114P10073	Ceramic: 180 pf ±10%, 100 VDCW; temp coef -3300	P2		
	10411202201	Earlier than REV A:  Contact, electrical: sim to Cambion 460-3232-	(4*	194116114910073	PPM. Added by REV A.			MULTI-FREQUENCY MODIFICATION KIT
	19A116366P1	ol-os.			TRANSISTORS			19A129762G1
J33	19A116356P2	Contact, electrical: sim to Cambion 460-3233-	Q1	19A129187P1	Silicon, PNP.			
and J34		01-03.	Q2	19A116201P3	Silicon, NPN.	sı	19B219976G1	Switch Assembly.
J35*	19A116366P4	Contact, electrical: sim to Concord 10-891-1.	Q2	19411620193	Sificon, NEW.	31	13821337661	United Assembly.
		Earlier than REV A:	1		RESISTORS			LOADING COIL ASSEMBLY 19C32O365G1
	19A116366P1	Contact, electrical: sim to Cambion 460-3232-01-03.	Rl	3R151P103J	Composition: 10K ohms ±5%, 1/8 w.			
		01 00.	R2	3R151P332J	Composition: 3.3K ohms ±5%, 1/8 w.			
		RELAYS	R3	3R151P154J	Composition: 150K ohms ±5%, 1/8 w.	Cl	19A116462P3	Variable: less than 2 pf to more than 20 pf, 100 VDCW, -320 PPM/°C.
K1*	19B209562P2	Hermetic sealed: between 45-100 ohms ±10%, 2 form C contacts, 5.0 VDC nominal, 1.0 w max operating;	R4	3R151P182J	Composition: 1.8K ohms ±5%, 1/8 w.			
		sim to GE 3SCS1002A2.			TERMINALS			
		In REV A:	El	19A116854P1	Terminal, solderless.	L1	19B219759G1	Coil, Includes:
	19B209562P1	Hermetic sealed: 98 ohms ±10%, 2 form C contacts, 6.0 VDC nominal, 1.0 w max operating; sim to GE					19B209436P1	Tuning slug.
		3SCS1001A2. Added by REV A.						MISCELLANEOUS
			F701	19A127884G1	Fuse Kit.		19B216897G3	Rear Cover Assembly. (See RC2623, items 61, 62).
Ll	19B209420P125	Coil, RF: 10.0 µh ±10%, 3.10 ohms DC res max;			JACKS AND RECEPTACLES		19B216897G4	Rear Cover Assembly. Clip type. (See RC2623,
and L2		sim to Jeffers 4446-4K.	J701	19B216594G2	Connector, female: 6 contacts.		10001076061	items 61, 63).  Antenna Assembly. (See RC2623, items 20-24).
		2222222	J702		See Mechanical Parts RC2623 items 14, 16.		19B219768G1	Battery, rechargeable. Nickel Cadmium.
		RESISTORS	J703		See Mechanical Parts RC2623 items 14, 51, 67.		19D413522G1 19A127884G1	Fuse Kit.
R1*	3R152P181J	Composition: 180 ohms ±5%, 1/4 w.	J704		See Mechanical Parts RC2623 items 54-56, 65, 71.		4038381P4	Alignment tool. Fork tip.
	an1500001 t	In REV A:  Composition: 220 ohms ±5%, 1/4 w.					19B219079G1	Alignment tool. Allen tip.
	3R152P221J	Composition: 220 onms 15%, 1/4 w.  Earlier than REV A:	K1*	19A127836G1	1		15522501561	
	3R151P391J	Composition: 390 ohms ±5%, 1/8 w.	"		Sensitive: 95 ohms ±10%, 2 form C contacts, 5.5 to 9.0 VDC (over the temp range indicated); sim to C.P. Clare MF1401G01. Deleted by REV B.			MECHANICAL PARTS (SEE RC2623)
R2	3R151P913J	Composition: 91K ohms ±5%, 1/8 w.						
R2 R4	3R151P913J	Composition: 10K ohms ±5%, 1/8 w.				1	19A116543P1	Cap screw, socket head: No. 2-56 x 1/4.
R5	3R151P2033	Composition: 2.2K ohms ±5%, 1/8 w.	P701	19A115834P4	Contact, electrical: sim to AMP 2-332070-9.	2	19C317394P4	Gasket.
R6	3R151P2225	Composition: 100 ohms ±10%, 1/8 w.	P704 and	19A127569G1	Plug: 8 contacts.	3	19B204527P2	Diaphragm: No. 2 inches dia.
and R7			P7 05			4	N681P5002C6	Screw, phillips head: No. 2-56 x 1/8.
R8	19A116412P9	Variable, cermet: 50K ohms ±10%, 0.5 w; sim to	P706*	19A127569G1	Plug: 8 contacts. Deleted by REV B.	5	19A127319P1	Nut: No. 1/4-32.
		Helipot Model 62 PR50K.	1		RESISTORS	6	4037064P18	Washer, non-metallic.
		SOCKETS	R707	19A116227P1	Resistor/switch: variable, carbon film, 25K ohms	7	N70BP703C6	Set screw: No. 3-48 x 3/16.
XK1*	19A115834P5	Contact, electrical: sim to AMP 3-331272-5.			±20%, 1/8 w, (Includes S703), SPST, 3 amps at 125 VAC; sim to Mallory Type MZC.	8	19B232784G1	Knob assembly. Includes items 7, 68.
		(Quantity 7). Deleted by REV A.	R708	19A116227P2	Variable, carbon film: 25K ohms ±10%, 1/8 w; sim	9	19B219768G1	Antenna assembly. (Includes items 20-23).
A705*		PUSH TO TALK SWITCH BOARD	1	001515155	to Mallory Type M/C.	10	19D413531P2	Grille (STANDARD).
		19B232586G2 (Added by REV F)	R709	3R151P152K	Composition: 1.5K ohms ±10%, 1/8 w.	,,	19B226502P2	Grille, (HI-POWER).
	1	CARACATORS	R710*	3R151P103K	Composition: 10K ohms ±10%, 1/8 w. Deleted by REV B.	11	NP270290P2	Nameplate (GE Monogram - STANDARD).
			1				NP270290P3	Nameplate. (GE Monogram - HI-POWER).
C1	19A116114P10073	Ceramic: 180 pf ±10%, 100 VDCW; temp coef -3300 PPM.						
сз	19A116114P10073	Ceramic: 180 pf ±10%, 100 VDCW; temp coef						
	1	-3300 PPM.	1					

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╛	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
	12	19D413542G14	Case assembly. (Includes items 14, 15, 18, 33-39, 48, 49).	62	19B216897G3	Rear Cover Assembly (without clip).
	13	19B216858P1	Insert.	63	19B216897G4 19A130397P1	Rear Cover Assembly (with clip). Strap.
- 1	14	19A127753P1	Contact. (Part of J702 and J703).	65	19A130586P1	Insulator.
.	15	19A134548P1	Insert, screw thread: No. 2-56.	66	19A11983P10	Seal.
- [	16	19B216862P2	Contact. (Part of J702).	67	4033198P18	Eyelet, metallic.
	17	19A127779G5	Antenna tube.	68	19A137254P1	Insert.
-1	18	19A116854P1	Terminal, solderless. (El).	69	4035630P1	Washer: teflon.
	19	19B216875P1	Support.	70		(Not Used).
	20	19C320383P3	Antenna rod. (Part of item 9).	71	19B232109P1	Button plug.
	21	19C320352P1	Bushing (Part of item 9).	72	19A127802P1	Rivet, shield.
.	22	N70P703C13	Set screw: No. 3-48 x 3/16.	73	19A116773P805	Tap screw, Phillips POZIDRIV®: No. 4-24 x 5/16.
1	23	19A129649P1	Antenna Cap. (Part of item 9).	74	19A130993P1	Gasket.
- 1	24	19B219770G1	Spacer Assembly. (Part of item 9).	75	N170P9004P2	Cap screw: No. 4-40 x 1/4.
- 1	25	19A116869P1	Tap screw: No. 2-32 x 1/4.			
-	26	19C32O359P1	Cover.			
	27	19A129559P1	Gasket.			
- 1	28	19C317050P1 19A129390P1	Protective Cover. Disc.			
-	30	19A130426G2	Knob.			
- 1	31	19B219540P1	Catch.			
- [	32	19B216520P4	washer, nylon: 1/4 inch.			
١	33	19A127319P2	Nut: No. 1/4-28.			
- 1	34	19B216926P8	Decorative cap. (TYPE 99).	1		
- 1	35	19C320721P1	Seal. (Used with TYPE 99 Switch).			
.	36	N41P1006	Screw, slotted, steel: No. 0-80 x 3/8. (Part of			
	37	19C328416G1	S701). Button assembly. (Part of S701).			
- 1	38	19C328407Pl	Collar. (Part of S701).			
-	39	19A137621P1	Plate. (Part of S701).	İ		
-	40	19A137620P1	Spring. (Part of S701).			
- 1	41	N207P1C6	Nut, hex: thd. size No. 0-80. (Part of S701).			
- 1	42	19B209643P2	Switch. (Part of S701).			
٠	43	19B216865Pl	Insulator (Part of S702).			
- 1	44	N647P5004C	Cap screw: 2-56 x 1/4. (Part of S702).			
	45	19B216864P1	Contact (Part of S702).			
	46	19B216863P1	Spring contact. (Part of S702).			
	47	N910P6C6	Retaining ring. (Part of S702).			
- 1	48	19A127754P1	Gasket (Part of S702).			
	49	19A127755P1	Spring (Part of S702).			
	50	19B216862P1	Contact (Part of S702).			
- 1	51	N330P605F22	Eyelet, brass: 1/16 x 5/32.  (Not Used).			
	52	N330P602F22	Strap.			
- 1	53 54	19A127762P1 19B216891G1	Spring assembly. (Part of J704).			
- 1	55	19D413467Pl	Fastener (Part of J704).			
- 1	56	19A115794P3	Flat head screw: steel, self-locking, 2-56 x 5/16.			
	1 55		(Part (Part of J704).			
	57	19B219799P1	(Not Used).			
	58	19C311491P3	Can. (Used with Regulator, Oscillator Compensator, and Compressor Circuits).			
-	59	19B219510Pl	Insulator. (Located between System and Receiver Boards).			
	60	19A116270P1	Tape, pressure sensitive. (Specify length).			
-	61	19C317394P6	Gasket.			
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VIEW "D" VIEW "F" RC-2623D

LBI4700

# PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

REV. A - System Board and Case Assembly 19D417103G4

Incorporated into initial shipment.

REV. B - To make compatible with more options. Changed Kl and printed wire runs.

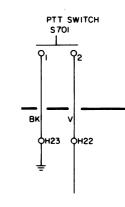
REV. C - To improve battery pack connector. Added insulator.

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REV. D - To improve case design.
Incorporated metal nuts for PTT switch mounting screws.

REV. E - To improve reliability and change Knobs. Added PTT switch A705. Changed S701. Changed Knobs.

Schematic Diagram was:



REV. A - System Board 19D417102G1

To make compatible with more options. Changed Kl and printed wire runs.

REV. B - To improve PTT relay performance. Changed K1 and R1.

REV. C - To incorporate a new 5.4V regulator module. Changed A2 and added C18.

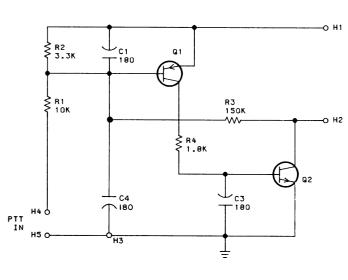
REV. A - PTT Switch 19B232586G1

To improve RF filtering. Added C4.

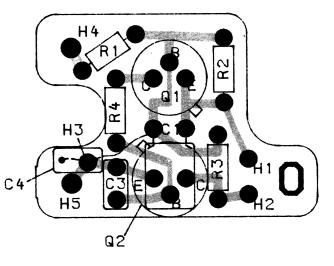
REV. F - System Board and Case Assembly 19D417103G4

To optimize performance. Change A705.

Schematic Diagram was:



Outline Diagram was:



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Figure 1 - Stop Post Adjustment

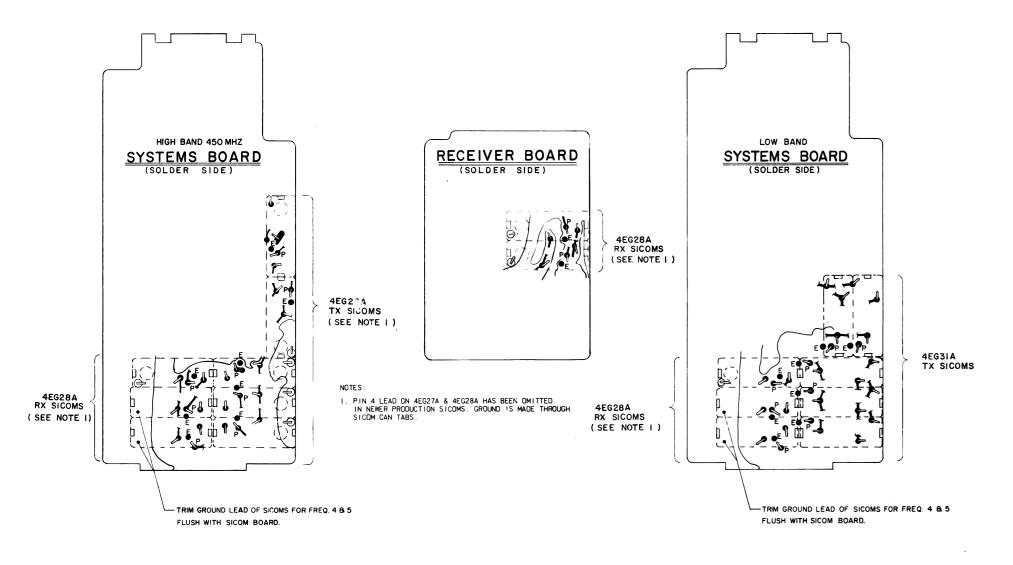
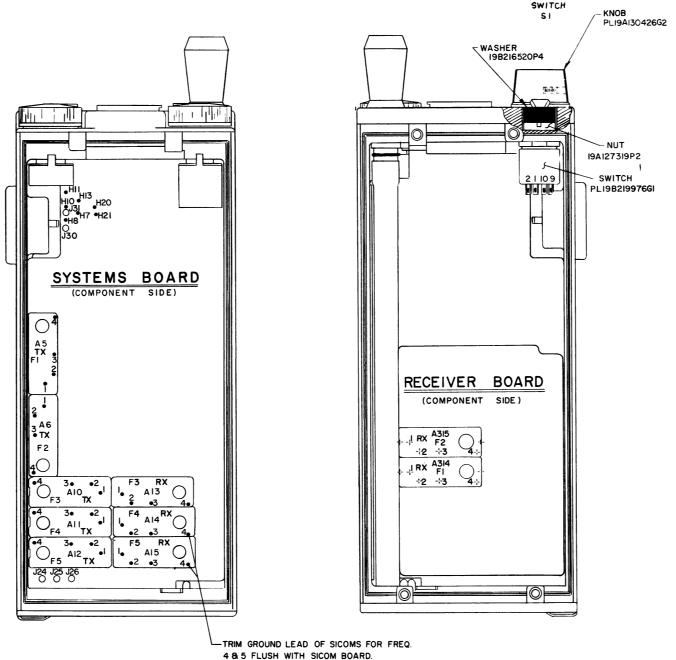


Figure 2 - Oscillator Module and Diode Installation

(19D417138, Sh. 2, Rev. 3)





MULTI-FREQUENCY

Figure 3 - Oscillator Mounting Positions & Sl Connection Points

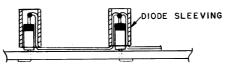


Figure 4 - Typical Diode Mounting

# (19D417138, Sh. 1, Rev. 2)

# MULTI-FREQUENCY MODIFICATIONS

(19D417138, Sh. 1, Rev. 2 & Sh. 2, Rev. 3)

The multi-frequency modifications include instructions for adjusting the stop post on multi-frequency switch S1, for adding oscillator modules, for repeating frequencies, and repeating oscillator modules.

#### 1- STOP POST ADJUSTMENT

----CAUTION-

Due to the small size of the stop posts, be very careful when making adjustments to avoid losing the stops.

- Remove the multi-frequency switch as directed in the Disassembly Procedure (see Table of Contents in LBI-4709).
- Turn the shaft fully counterclockwise as viewed from the knob end.
- Unscrew the panel seal to gain access to the stop post (see Figure 1).
- Install the stop post in the appropriate hole as shown in the following chart.

NO. OF FREQS	MOVE ADJUSTABLE STOP TO
2	Н2
3	Н3
4	Н4
5	Н5

- Replace the panel seal with the side marked "Bottom" against surface "Z".
- 6. Re-install the Multifrequency Switch.

# 2- ADDING OSCILLATOR MODULES

 After completing the stop post adjustment, connect the leads from multi-frequency switch S1 as shown in the following chart (see Figure 3 for connection points). Tape back all unused leads.

CONNECTION CHART					
FROM	то	WIRE COLOR	S1 POSITION		
S1-C1	Hll (solder)	SFT-BL			
S1-1	J31 SFT-W-BK		1		
S1-2	J30	J30 SFT-W-O			
S1-3	J24	BR	3		
S1-4	J25	R	4		
S1-5	J26	0	5		
	·				

 Place the oscillator module(s) in the proper holes (see Figure 3). Then bend over tabs on the can and solder to the adjacent pads (see Figure 2).

- Bend the leads of the oscillator module as shown in Figure 2 (or appropriate Outline Diagram) and solder to the adjacent pads.
- 4. For two or more transmitter frequencies and one receiver frequency, remove the jumper from H7 to H10 and add a sleeved jumper (#26 AWG) from H7 to H13 on the Systems Board
- 5. For two or more receiver frequencies and one transmitter frequency, remove the jumper from H8 to H10 and add a sleeved jumper (#26 AWG) from H20 and H21 on the Systems Board.

## 3- REPEATING FREQUENCIES

For repeating both transmitter <u>and</u> receiver frequencies without adding additional oscillator modules, add a sleeved jumper (#26 AWG) between the frequencies to be repeated. For example, if transmitter and receiver channels 1 and 5 are to be repeated, add

## 4- REPEATING OSCILLATOR MODULES

To repeat frequencies for the transmitter only or the receiver only, diodes can be used in place of oscillator modules.

- 1. Set the stop on S1 and install the oscillator modules whose frequencies are <u>not</u> to be repeated as directed in Section I and II.
- 2. Install the oscillator(s) whose frequencies are to be repeated as directed above except solder the Number 2 pin to the "E" pad instead of the "P" pad (see Figure 2).
- 3. For every channel that a frequency is being repeated, assemble a diode (5494922P1) in the space normally intended for the oscillator module by putting the annode lead in the Number 2 hole, bending it over and soldering to the "P" pad. The cathode lead will be terminated later.
- 4. For each different frequency that is repeated, an addition diode (5494922Pl) is to be assembled in respective channel closest to the oscillator module being repeated. Assemble the diode in the Number 1 hole, annode lead down and sleeved, and connect to the associated "E" pad. Then run the jumper from this pad to the "P" pad of related oscillator module.

The cathode end of the diodes should be connected together using mid air connections. Make the connection and run the wire down the side of the diode along the component side of the board to the next diode, and so on until all the diode's cathodes are connected together. Route these wires to give the shortest connections. Now connect a lead to the cathode of the diode that is closest to the repeated oscillator module and run this lead down the side of the diode and through any empty hole or slot to the solder side of the board, and connect the lead to the "E" pad of the oscillator module. Next sleeve the diodes as shown in Figure 4.

Example: Channel 3 and 4 to be same as Channel 1.
Channel 1 and 5 to be same as Channel 2.
(This example applies TX Frequencies only).

- 1. Assemble the oscillator module in Channels 1 and 2 as normal except connect the Number 2 lead to the "E" pad instead of
- 2. Assemble (1) diode in the Number 2 hole, anode lead down, in each of Channels 1, 3, 4 & 5 and solder to "P" pads.
- 3. Since two frequencies are being repeated, two additional diodes will be required, one in the Number 1 hole of Channel 3 and the other in the Number 1 hole of Channel 5. Sleeve, bend, and solder leads to the "E" pad. Connect jumper between the "E" pad of the Number 3 Channel and "P" pad of oscillator module Number 1. Connect a jumper between the "E" pad of Number 5 Channel and "P" pad of oscillator module Number 2.
- 4. Connect the top lead (cathode) of diodes (3) in Channel 3 and 4 to each other by soldering jumper wire to leads, dressing the wire down the side of the diodes and along the board. Connect a jumper from the top of diode in the Number 1 hole of Channel 3 to the "E" pad of oscillator module Number 1. Run the wire down through the board using any available hole or slot to the solder side. Connect the jumper from the diode in Channel Number 5 to oscillator module Number 2 in the same manner.

Issue 3